

MAGNETIC TUNNEL JUNCTION CAP STRUCTURE AND METHOD FOR FORM- ING THE SAME

Abstract

A magnetic random access memory (MRAM) device includes a cap layer formed over a magnetic tunnel junction (MTJ) stack layer, an etch stop layer formed over the first cap layer, and a hardmask layer formed over the etch stop layer. The etch stop layer is selected from a material such that an etch chemistry used for removing the hardmask layer has selectivity against etching the etch stop layer material.